

IGBT

Low $V_{CE(sat)}$ IGBT in TRENCHSTOP™ 5 technology copacked with RAPID 1 fast and soft antiparallel diode

IKZ75N65EL5

650V DuoPack IGBT and diode
Low $V_{CE(sat)}$ series fifth generation

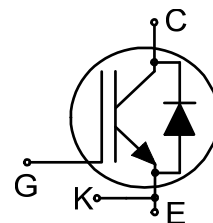
Data sheet

Low $V_{CE(sat)}$ IGBT in TRENCHSTOP™ 5 technology copacked with RAPID 1 fast and soft antiparallel diode

Features and Benefits:

Low $V_{CE(sat)}$ L5 technology offering

- Very low collector-emitter saturation voltage $V_{CE(sat)}$
- Best-in-Class tradeoff between conduction and switching losses
- 650V breakdown voltage
- Low gate charge Q_G
- Maximum junction temperature 175°C
- Qualified according to JEDEC for target applications
- Pb-free lead plating
- RoHS compliant
- Complete product spectrum and PSpice models:
<http://www.infineon.com/igbt/>



Applications:

- Uninterruptible power supplies
- Solar photovoltaic inverters
- Welding machines

Package pin definition:

- Pin C & backside - collector
- Pin E - emitter
- Pin K - Kelvin emitter
- Pin G - gate

Please note: The emitter and Kelvin emitter pins are not exchangeable. Their exchange might lead to malfunction.



Key Performance and Package Parameters

Type	V_{CE}	I_C	$V_{CE(sat)}$, $T_{vj}=25^\circ\text{C}$	T_{vjmax}	Marking	Package
IKZ75N65EL5	650V	75A	1.1V	175°C	K75EEL5	PG-TO247-4

Table of Contents

Description	2
Table of Contents	3
Maximum Ratings	4
Thermal Resistance	4
Electrical Characteristics	5
Electrical Characteristics Diagrams	7
Package Drawing	14
Testing Conditions	15
Revision History	16
Disclaimer	16

Maximum Ratings

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	V_{CE}	650	V
DC collector current, limited by $T_{vjmax}^{1)}$ $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	I_C	100.0 100.0	A
Pulsed collector current, t_p limited by $T_{vjmax}^{2)}$	I_{Cpuls}	300.0	A
Turn off safe operating area $V_{CE} \leq 650\text{V}$, $T_{vj} \leq 175^{\circ}\text{C}$, $t_p = 1\mu\text{s}^{2)}$	-	300.0	A
Diode forward current, limited by T_{vjmax} $T_C = 25^{\circ}\text{C}$ value limited by bondwire $T_C = 100^{\circ}\text{C}$	I_F	90.0 89.0	A
Diode pulsed current, t_p limited by $T_{vjmax}^{2)}$	I_{Fpuls}	300.0	A
Gate-emitter voltage Transient Gate-emitter voltage ($t_p \leq 10\mu\text{s}$, $D < 0.010$)	V_{GE}	± 20 ± 30	V
Power dissipation $T_C = 25^{\circ}\text{C}$ Power dissipation $T_C = 100^{\circ}\text{C}$	P_{tot}	536.0 268.0	W
Operating junction temperature	T_{vj}	$-40 \dots +175$	$^{\circ}\text{C}$
Storage temperature	T_{stg}	$-55 \dots +150$	$^{\circ}\text{C}$
Soldering temperature, ³⁾ wave soldering 1.6mm (0.063in.) from case for 10s		260	$^{\circ}\text{C}$
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction - case	$R_{th(j-c)}$		0.28	K/W
Diode thermal resistance, junction - case	$R_{th(j-c)}$		0.46	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		40	K/W

¹⁾ Both values limited by bondwires.

²⁾ Defined by design. Not subject to production test.

³⁾ Package not recommended for surface mount applications.

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0V, I_C = 0.20mA$	650	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE} = 15.0V, I_C = 75.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 100^{\circ}C$ $T_{vj} = 150^{\circ}C$	- - -	1.10 1.11 1.12	1.35 - -	V
Diode forward voltage	V_F	$V_{GE} = 0V, I_F = 75.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 100^{\circ}C$ $T_{vj} = 150^{\circ}C$	- - -	1.40 1.42 1.40	1.70 - -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 1.00mA, V_{CE} = V_{GE}$	4.2	5.0	5.8	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 650V, V_{GE} = 0V$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 150^{\circ}C$ $T_{vj} = 175^{\circ}C$	- - -	- 1000.0 5000.0	40.0 - -	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0V, V_{GE} = 20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE} = 20V, I_C = 75.0A$	-	155.0	-	S

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C _{ies}	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz	-	12100	-	pF
Output capacitance	C _{oes}		-	150	-	
Reverse transfer capacitance	C _{res}		-	42	-	
Gate charge	Q _G	V _{CC} = 520V, I _C = 75.0A, V _{GE} = 15V	-	436.0	-	nC
Internal emitter inductance ¹⁾ measured 5mm (0.197 in.) from case	L _E		-	13.0	-	nH

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$						
Turn-on delay time	$t_{d(\text{on})}$	$T_{vj} = 25^{\circ}\text{C}$, $V_{CC} = 400\text{V}$, $I_C = 75.0\text{A}$, $V_{GE} = 0.0/15.0\text{V}$, $R_{G(\text{on})} = 23.0\Omega$, $R_{G(\text{off})} = 4.0\Omega$, $L\sigma = 30\text{nH}$, $C\sigma = 30\text{pF}$ $L\sigma$, $C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	120	-	ns
Rise time	t_r		-	23	-	ns
Turn-off delay time	$t_{d(\text{off})}$		-	275	-	ns
Fall time	t_f		-	50	-	ns
Turn-on energy	E_{on}		-	1.57	-	mJ
Turn-off energy	E_{off}		-	3.20	-	mJ
Total switching energy	E_{ts}		-	4.77	-	mJ

¹⁾ The internal emitter inductance does not affect the gate control circuitry if bypassed by using the Kelvin emitter pin.

Diode Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 25^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 75.0\text{A},$ $di_F/dt = 2000\text{A}/\mu\text{s}$	-	59	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.30	-	μC
Diode peak reverse recovery current	I_{rrm}		-	37.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-2400	-	A/ μs

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

IGBT Characteristic, at $T_{vj} = 150^{\circ}\text{C}$

Turn-on delay time	$t_{d(on)}$	$T_{vj} = 150^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 75.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(on)} = 23.0\Omega, R_{G(off)} = 4.0\Omega,$ $L\sigma = 30\text{nH}, C\sigma = 30\text{pF}$ $L\sigma, C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	106	-	ns
Rise time	t_r		-	27	-	ns
Turn-off delay time	$t_{d(off)}$		-	330	-	ns
Fall time	t_f		-	144	-	ns
Turn-on energy	E_{on}		-	2.12	-	mJ
Turn-off energy	E_{off}		-	5.10	-	mJ
Total switching energy	E_{ts}		-	7.22	-	mJ

Diode Characteristic, at $T_{vj} = 150^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 150^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 75.0\text{A},$ $di_F/dt = 2000\text{A}/\mu\text{s}$	-	79	-	ns
Diode reverse recovery charge	Q_{rr}		-	2.86	-	μC
Diode peak reverse recovery current	I_{rrm}		-	57.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	-1950	-	A/ μs

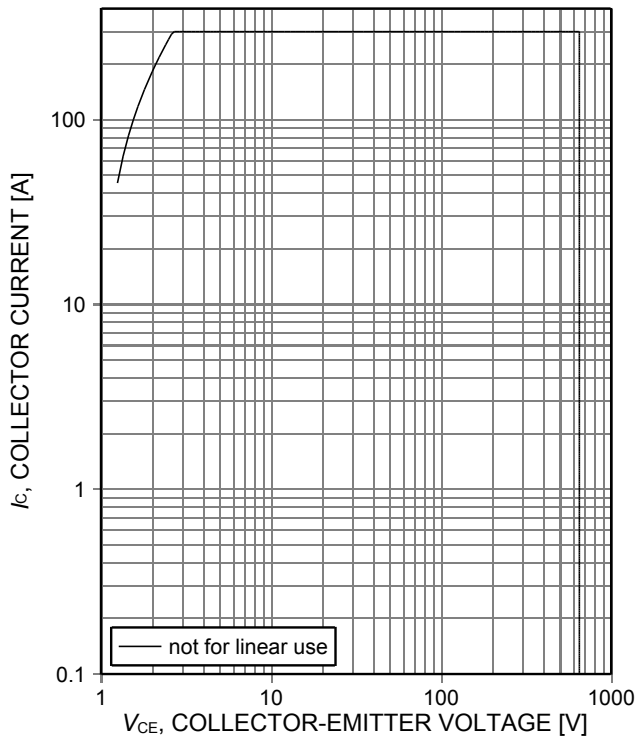


Figure 1. **Forward bias safe operating area**
($D=0$, $T_C=25^\circ\text{C}$, $T_{vj}\leq 175^\circ\text{C}$, $V_{GE}=15\text{V}$, $t_p=1\mu\text{s}$,
 I_{Cmax} defined by design - not subject to
production test)

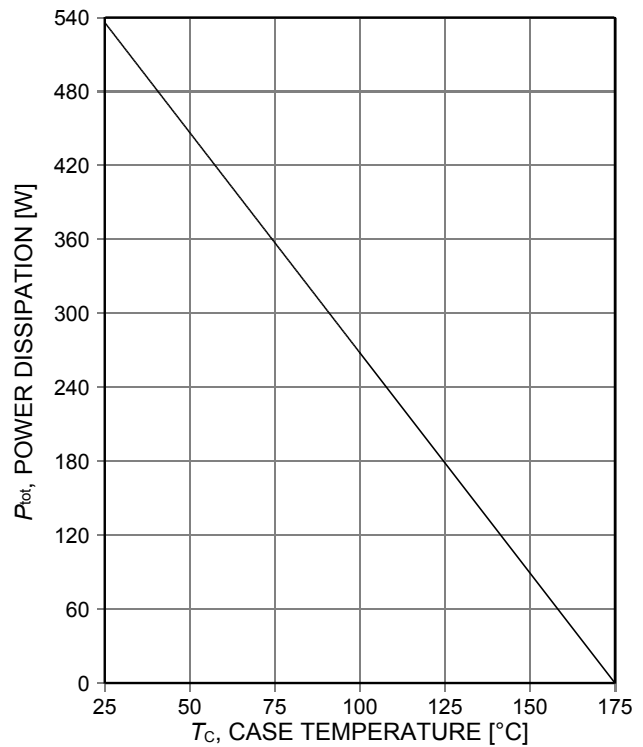


Figure 2. **Power dissipation as a function of case temperature**
($T_{vj}\leq 175^\circ\text{C}$)

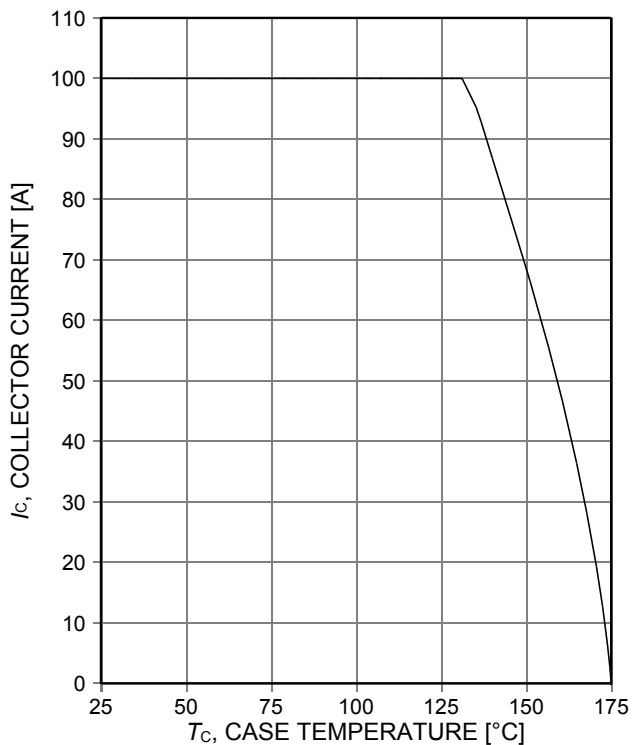


Figure 3. **Collector current as a function of case temperature**
($V_{GE}\geq 15\text{V}$, $T_{vj}\leq 175^\circ\text{C}$)

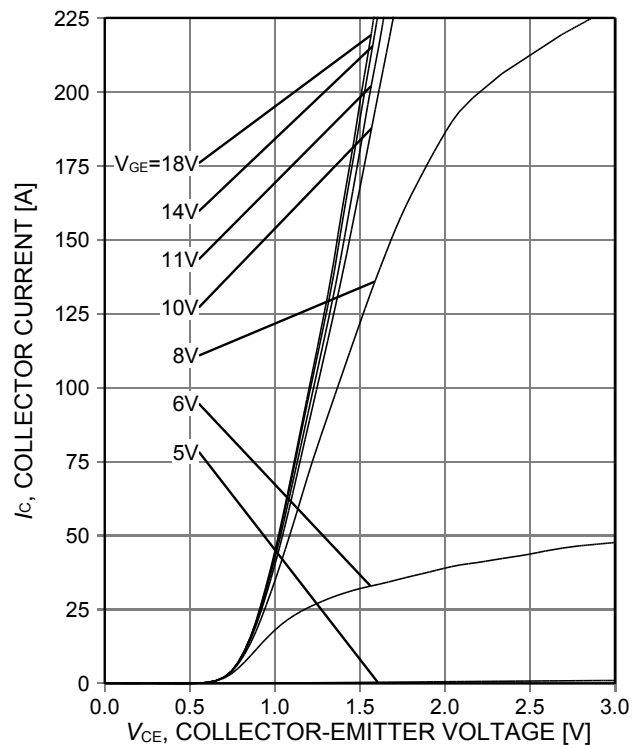


Figure 4. **Typical output characteristic**
($T_{vj}=25^\circ\text{C}$)

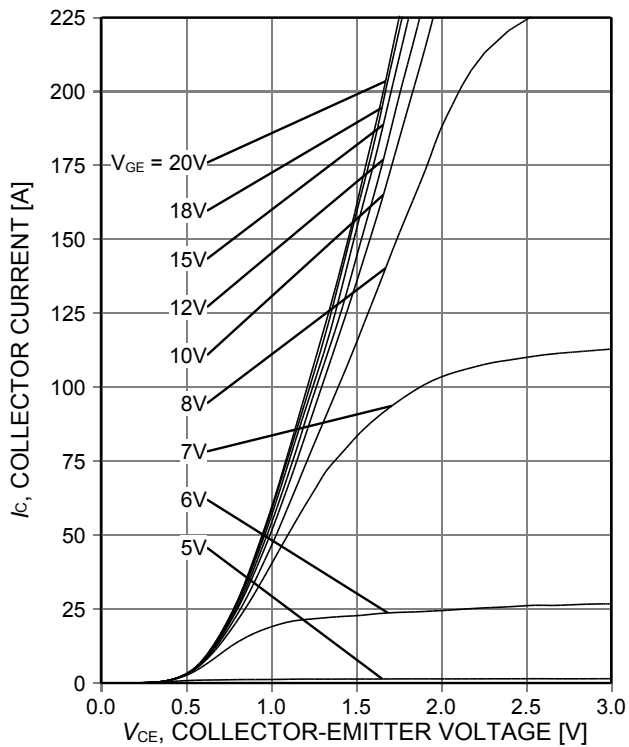


Figure 5. **Typical output characteristic**
($T_{vj}=175^{\circ}\text{C}$)

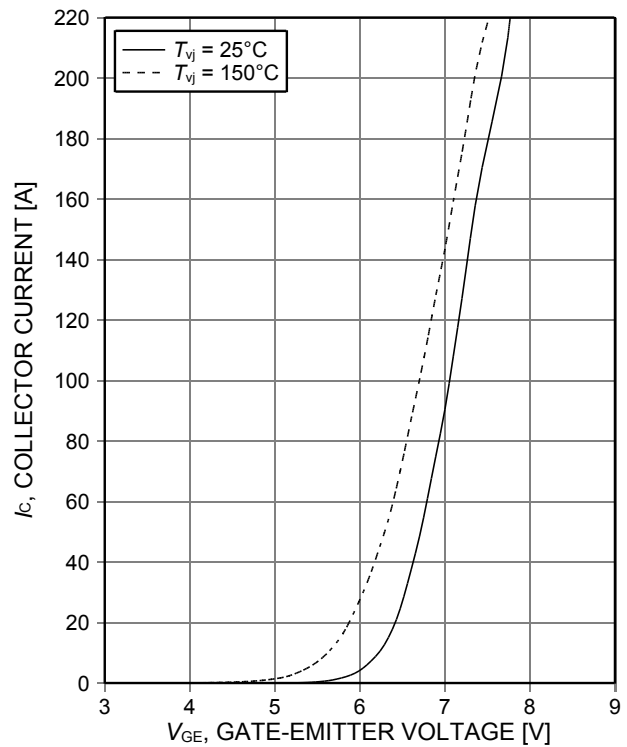


Figure 6. **Typical transfer characteristic**
($V_{CE}=20\text{V}$)

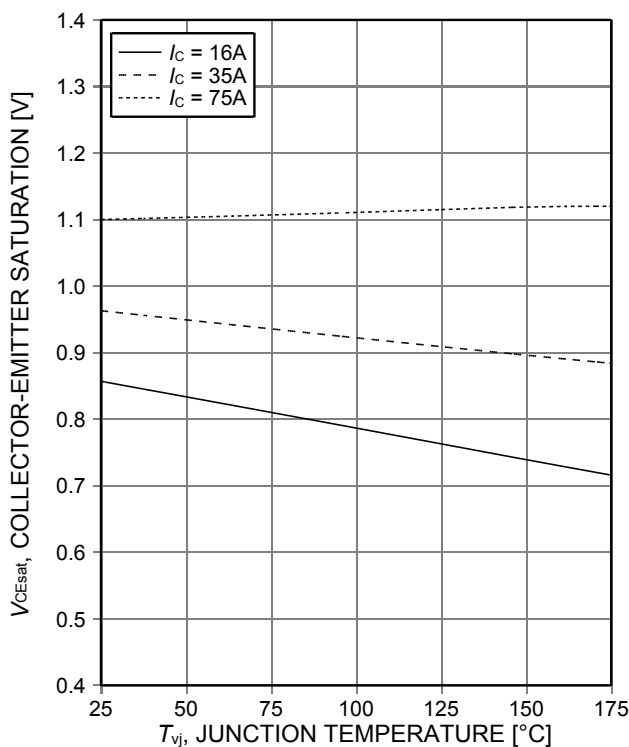


Figure 7. **Typical collector-emitter saturation voltage as a function of junction temperature**
($V_{GE}=15\text{V}$)

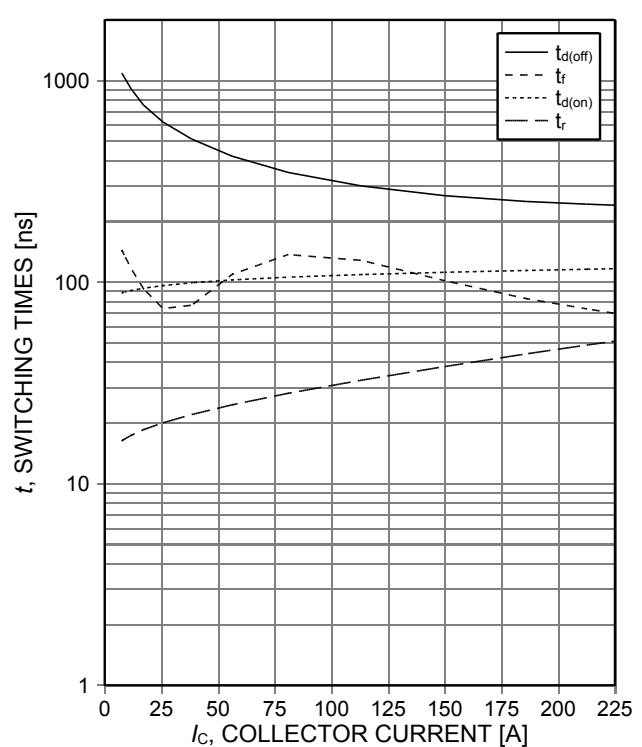


Figure 8. **Typical switching times as a function of collector current**
(inductive load, $T_{vj}=150^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $R_{G(on)}=23\Omega$, $R_{G(off)}=4\Omega$, dynamic test circuit in Figure E)

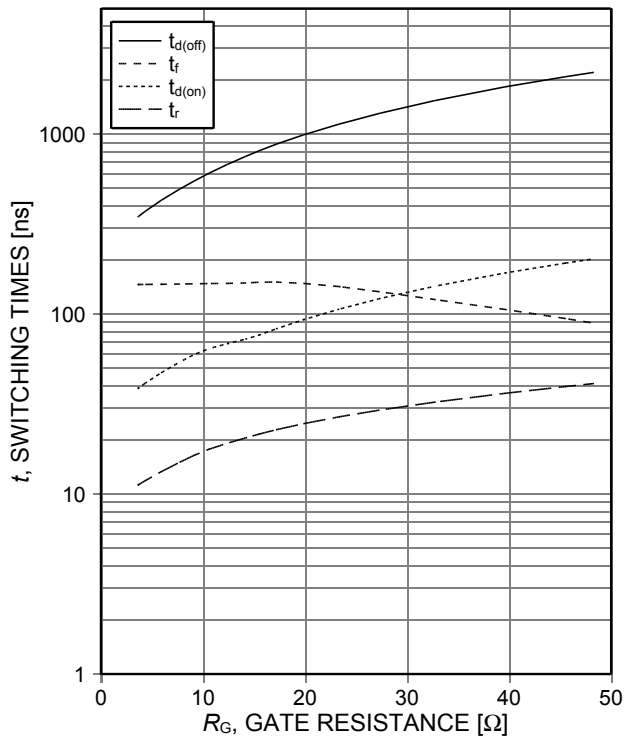


Figure 9. **Typical switching times as a function of gate resistance**
(inductive load, $T_{vj}=150^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=75\text{A}$, dynamic test circuit in Figure E)

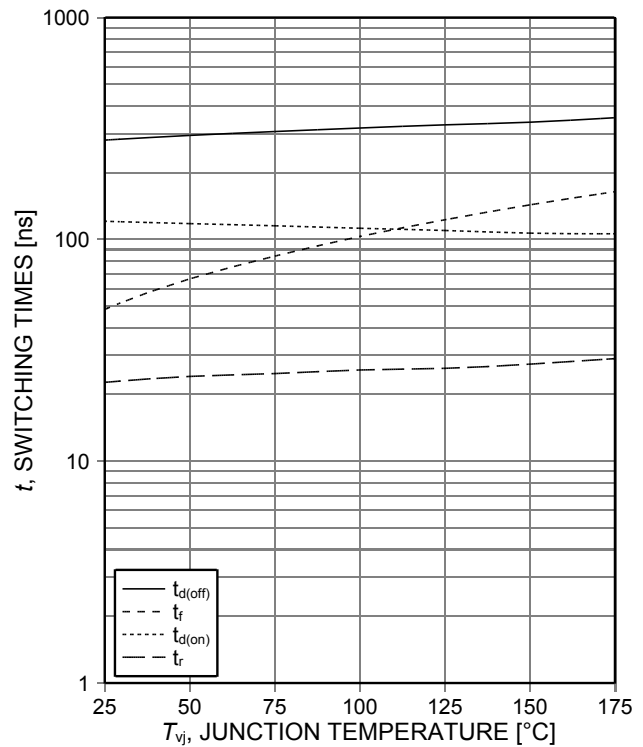


Figure 10. **Typical switching times as a function of junction temperature**
(inductive load, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=75\text{A}$, $R_{G(on)}=23\Omega$, $R_{G(off)}=4\Omega$, dynamic test circuit in Figure E)

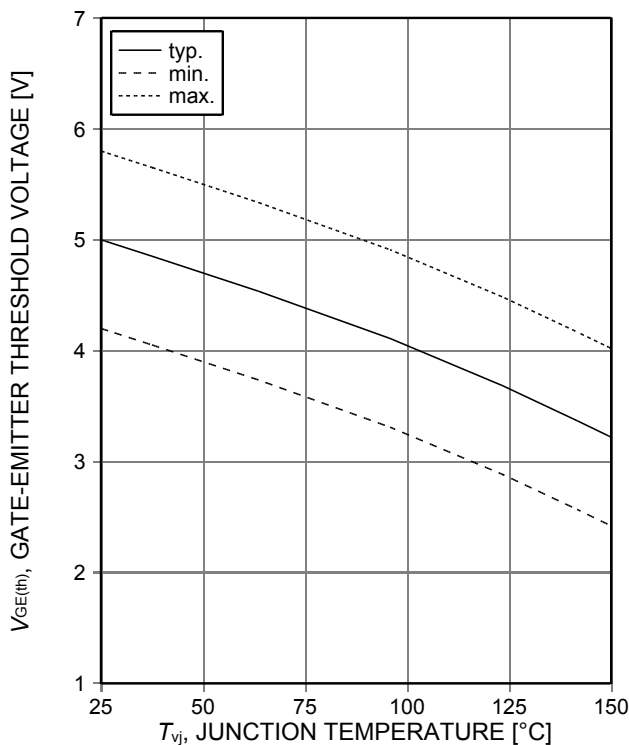


Figure 11. **Gate-emitter threshold voltage as a function of junction temperature**
($I_C=1\text{mA}$)

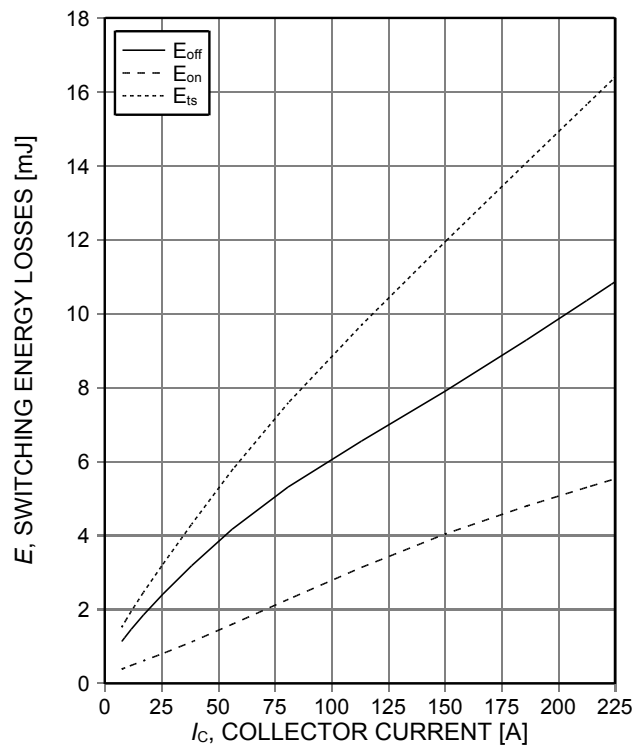


Figure 12. **Typical switching energy losses as a function of collector current**
(inductive load, $T_{vj}=150^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $R_{G(on)}=23\Omega$, $R_{G(off)}=4\Omega$, dynamic test circuit in Figure E)

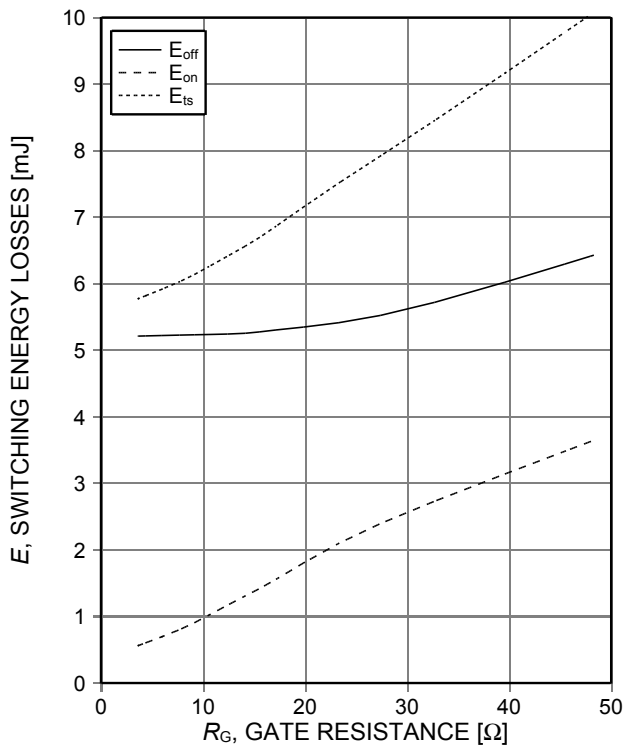


Figure 13. **Typical switching energy losses as a function of gate resistance**
(inductive load, $T_{vj}=150^{\circ}\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=75\text{A}$, dynamic test circuit in Figure E)

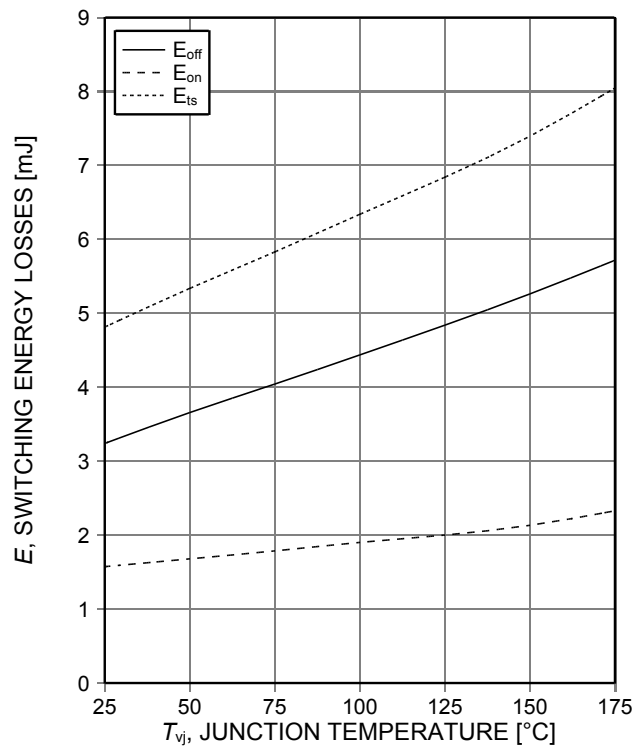


Figure 14. **Typical switching energy losses as a function of junction temperature**
(inductive load, $V_{CE}=400\text{V}$, $V_{GE}=0/15\text{V}$, $I_C=75\text{A}$, $R_{G(on)}=23\Omega$, $R_{G(off)}=4\Omega$, dynamic test circuit in Figure E)

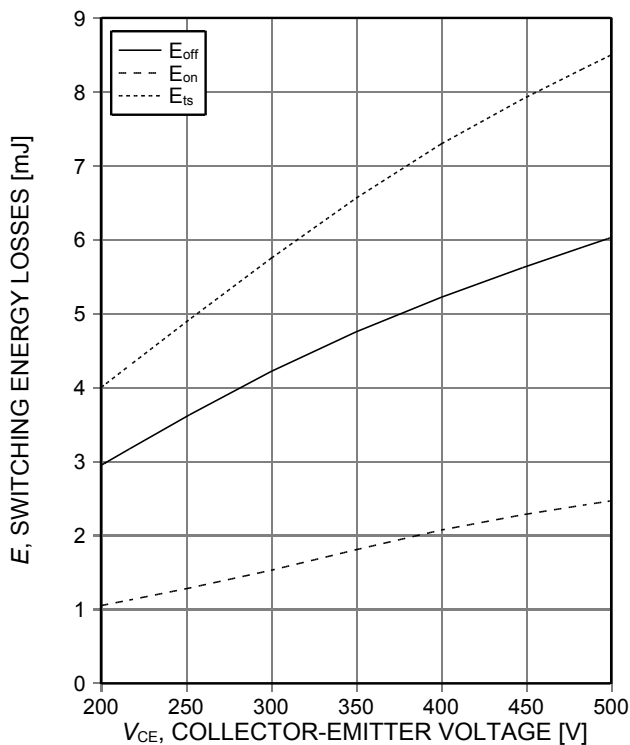


Figure 15. **Typical switching energy losses as a function of collector emitter voltage**
(inductive load, $T_{vj}=150^{\circ}\text{C}$, $V_{GE}=0/15\text{V}$, $I_C=75\text{A}$, $R_{G(on)}=23\Omega$, $R_{G(off)}=4\Omega$, dynamic test circuit in Figure E)

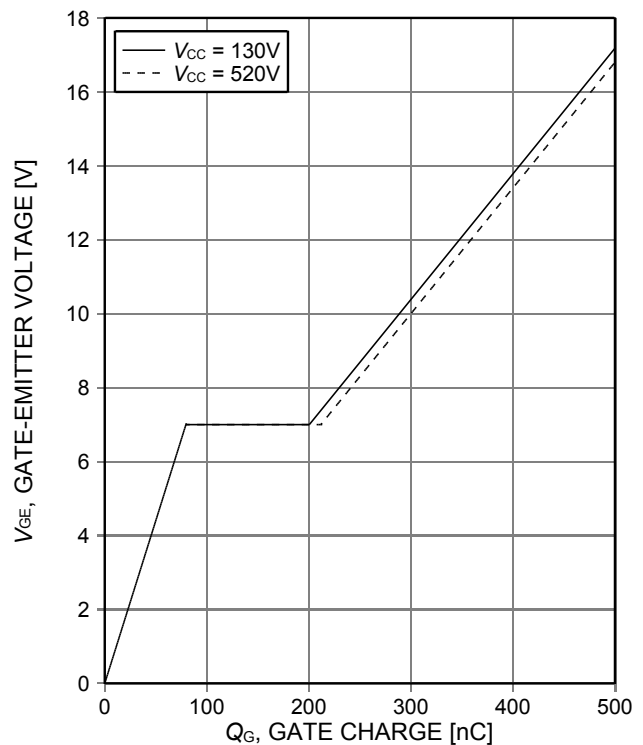


Figure 16. **Typical gate charge**
($I_C=75\text{A}$)

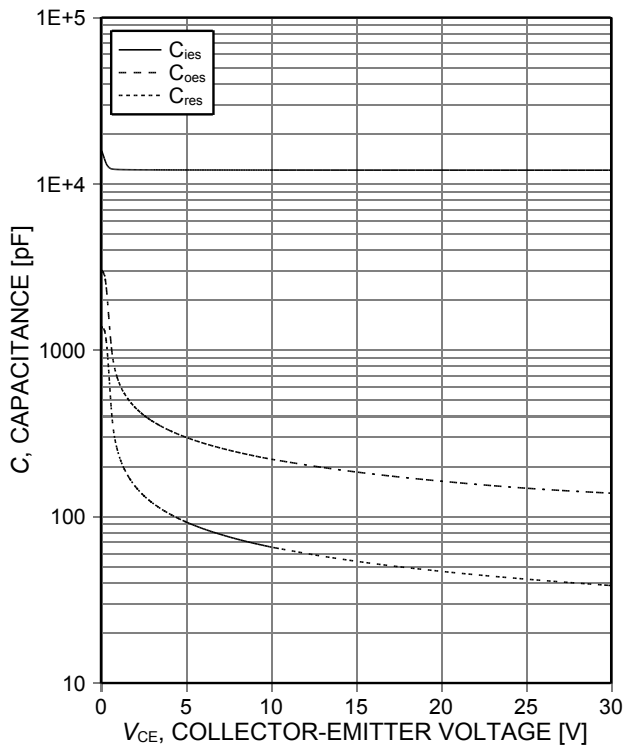


Figure 17. Typical capacitance as a function of collector-emitter voltage ($V_{GE}=0V$, $f=1MHz$)

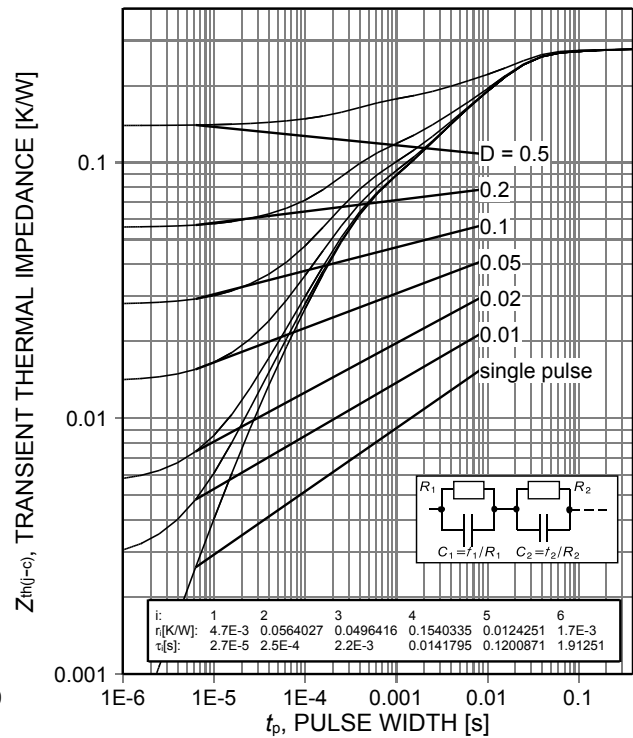


Figure 18. IGBT transient thermal impedance ($D=t_p/T$)

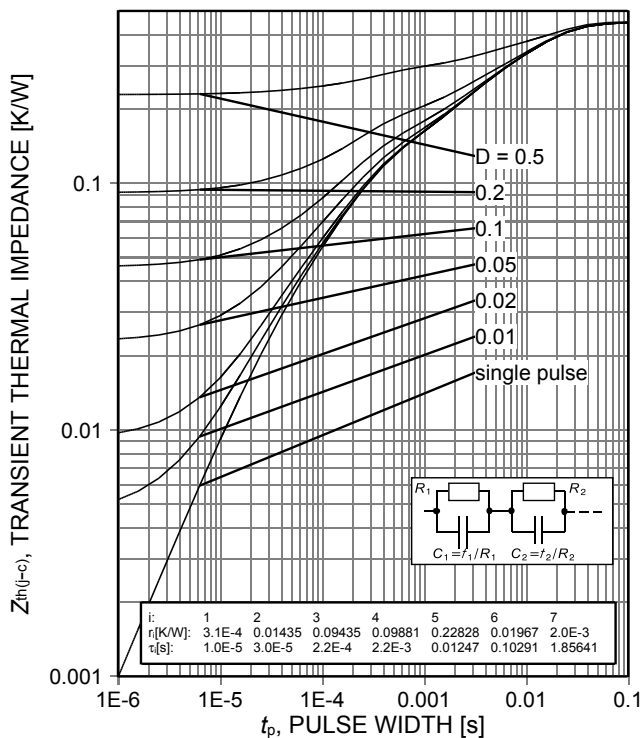


Figure 19. Diode transient thermal impedance as a function of pulse width ($D=t_p/T$)

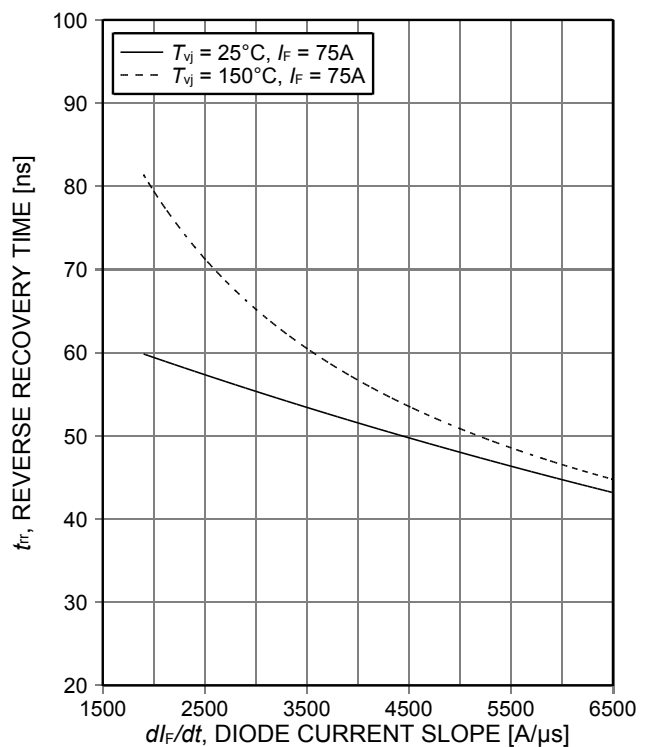


Figure 20. Typical reverse recovery time as a function of diode current slope ($V_R=400V$)

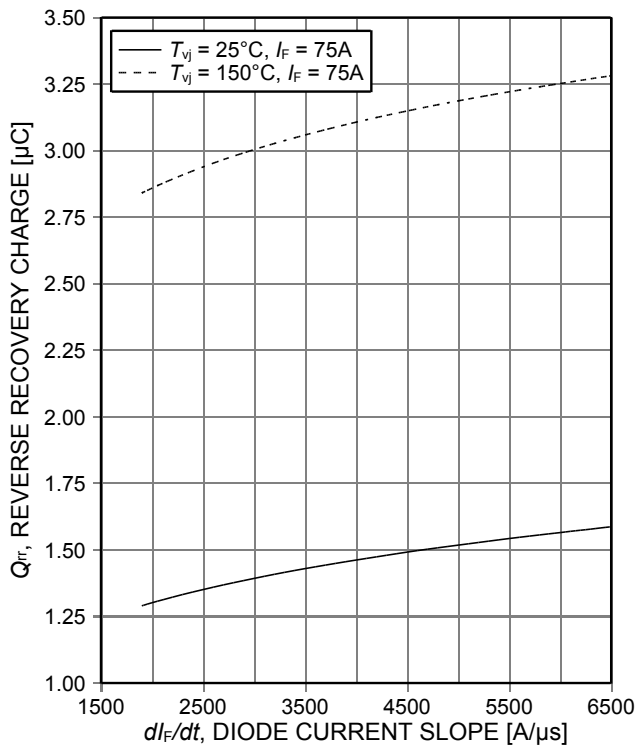


Figure 21. **Typical reverse recovery charge as a function of diode current slope**
($V_R=400V$)

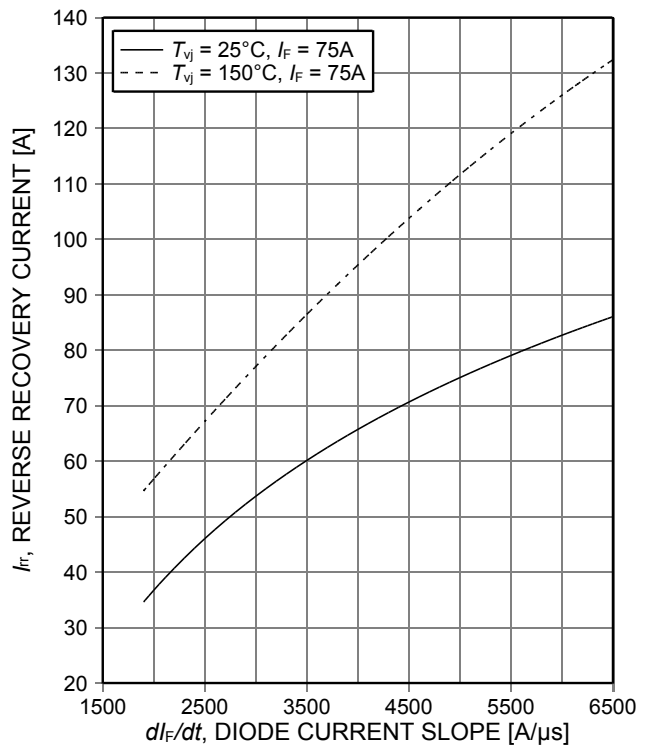


Figure 22. **Typical reverse recovery current as a function of diode current slope**
($V_R=400V$)

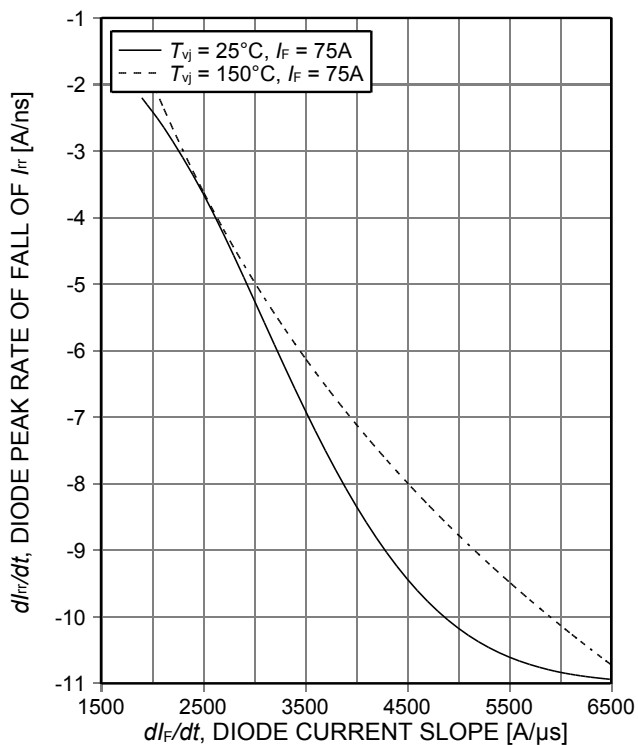


Figure 23. **Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**
($V_R=400V$)

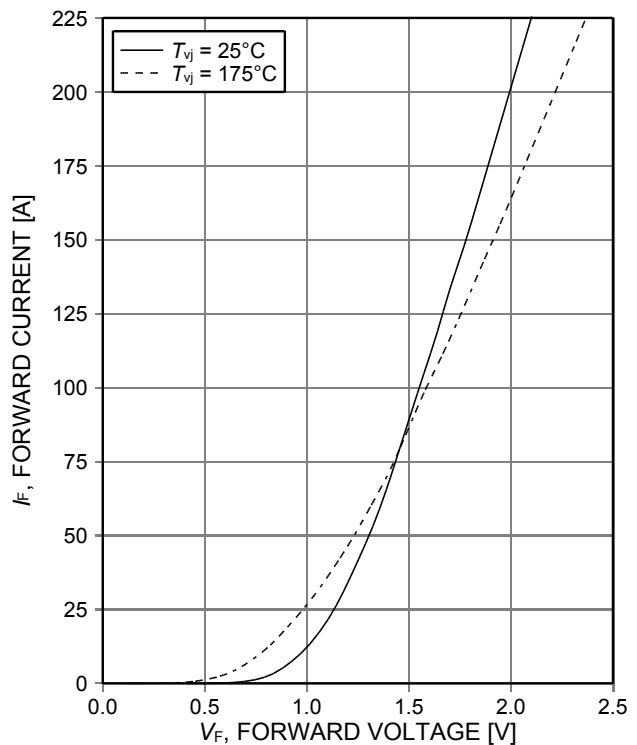


Figure 24. **Typical diode forward current as a function of forward voltage**

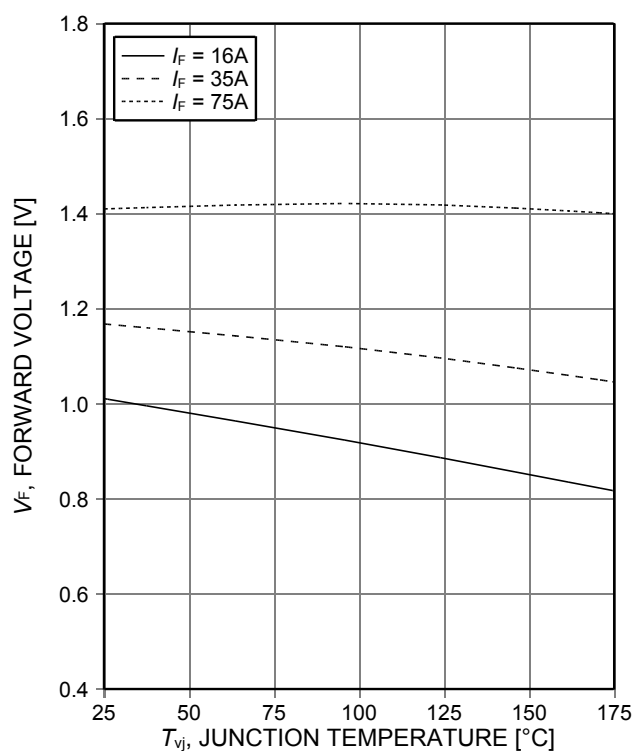
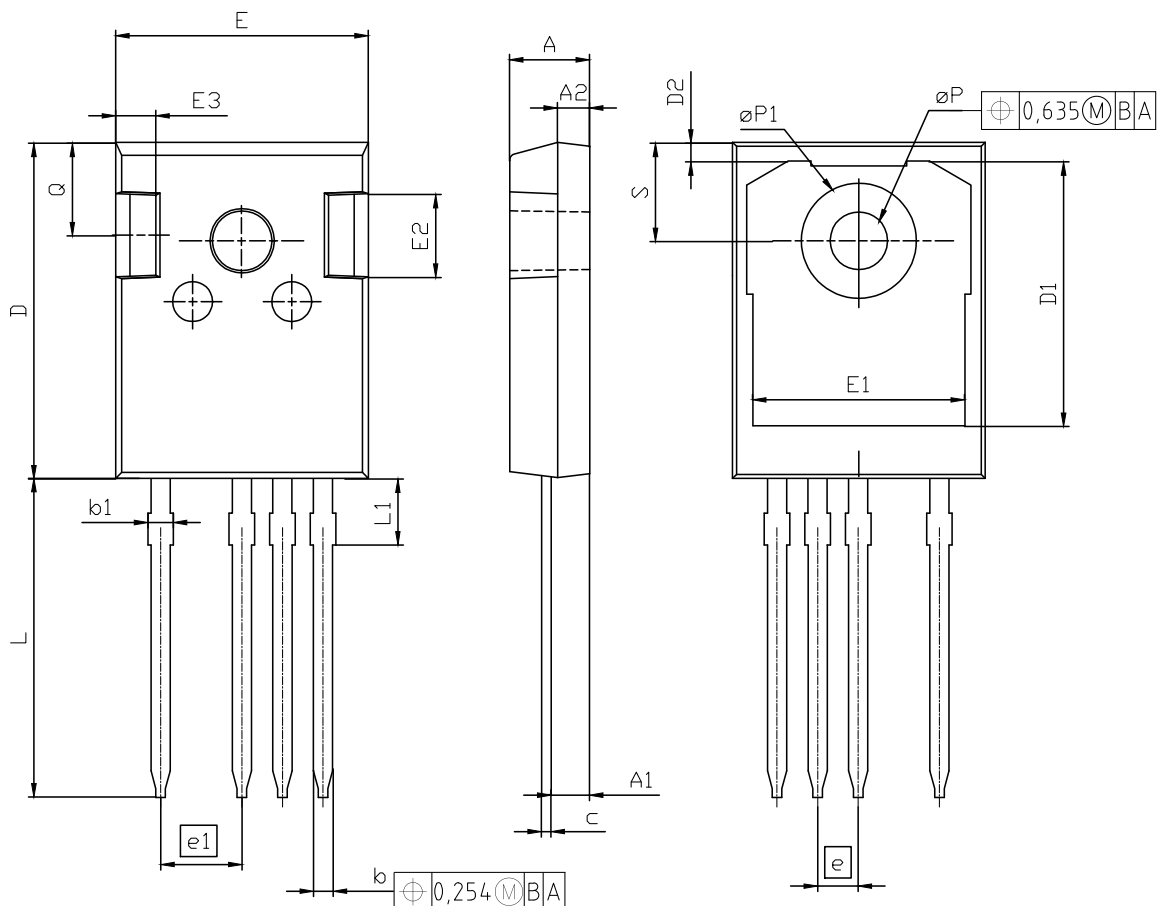


Figure 25. **Typical diode forward voltage as a function of junction temperature**

PG-TO247-4



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.29	2.54	0.090	0.100
A2	1.90	2.16	0.075	0.085
b	1.07	1.33	0.042	0.052
b1	1.10	1.70	0.043	0.067
c	0.50	0.70	0.020	0.028
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	2.54 (BSC)		0.100 (BSC)	
e1	5.08		0.200	
N	4		4	
L	19.72	20.32	0.776	0.800
L1	4.02	4.40	0.158	0.173
ϕP	3.50	3.70	0.138	0.146
$\phi P1$	7.00	7.40	0.276	0.291
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

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EUROPEAN PROJECTION 
ISSUE DATE 29-01-2013
REVISION 1

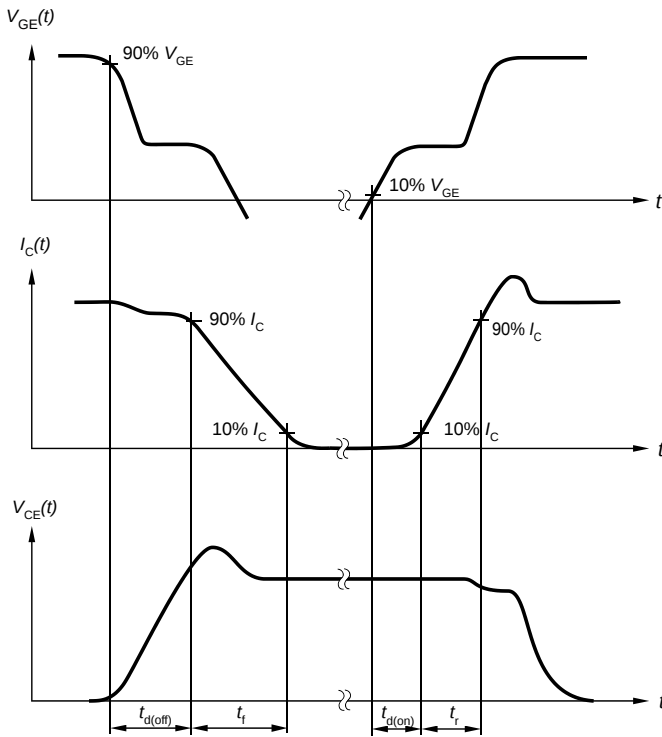


Figure A. Definition of switching times

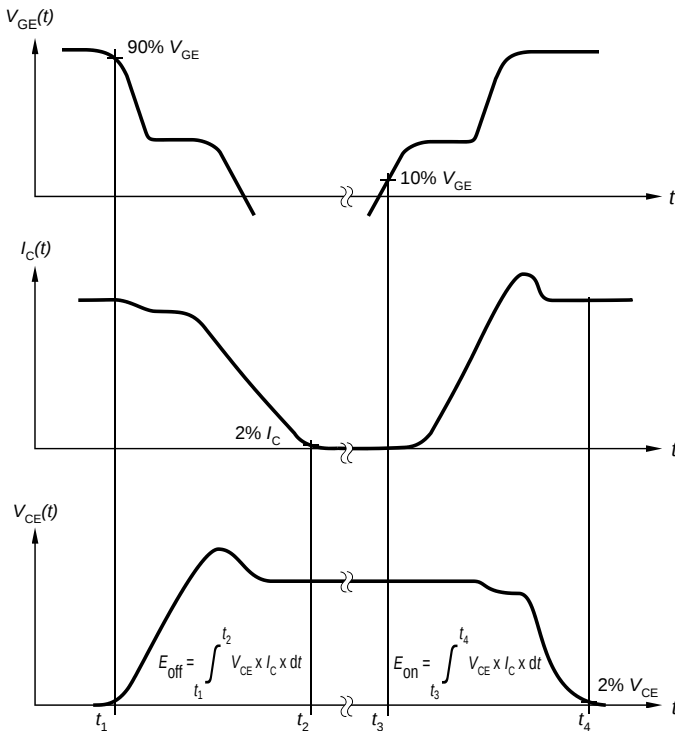


Figure B. Definition of switching losses

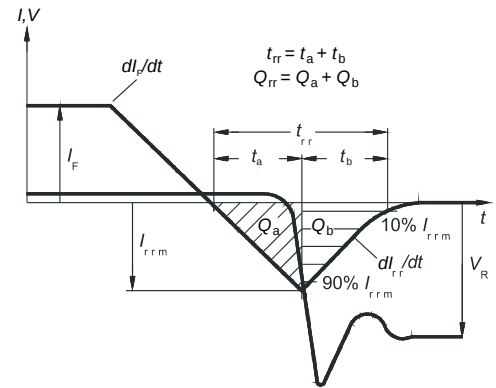


Figure C. Definition of diode switching characteristics

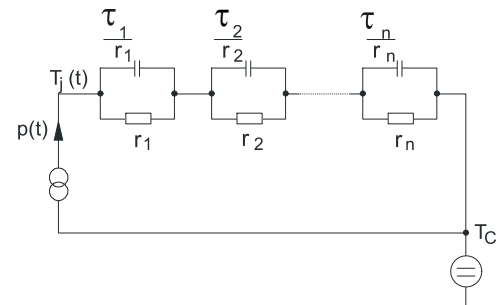
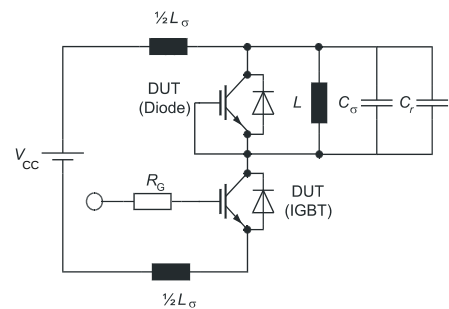


Figure D. Thermal equivalent circuit


Figure E. Dynamic test circuit
Parasitic inductance L_{σ} ,
parasitic capacitor C_{σ} ,
relief capacitor C_r ,
(only for ZVT switching)

Revision History

IKZ75N65EL5

Revision: 2014-12-10, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2014-12-10	Final data sheet

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Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели,
кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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